

AMENDMENTS TO THE CLAIMS:

Please amend Claims 1, 2, and 4 through 7 and add Claims 9 through 13 as follows:

1. (Currently Amended) A solid state image pick-up device formed on a chip, comprising:

a first scanning means, and

a pixel region;

a first shift register for reading a signal charge from the pixel region;

a second scanning means shift register having a lower driving frequency than that of the first scanning means shift register, wherein the first scanning means and the and second scanning means shift registers are arranged to be adjacent to along respectively different side portions of [[a]] the chip; respectively,

an amplifier for amplifying the signal charge read from the pixel region by the first shift register; and

wherein a predetermined a pad for outputting an output of the amplifier to an outside of the chip, the pad being arranged along a side portion of the chip different from the side portion along which the first shift register is arranged is arranged in at least one of side portions of the chip, except for the side portion on a side where the first scanning means is arranged.

2. (Currently Amended) A solid state image pick-up device according to claim 1, further comprising a wherein in the pixel region, on the chip, in which pixels having an active element are two-dimensionally arranged[[,]]

~~wherein the predetermined pad includes at least a pad through which a voltage or a ground potential is applied to the active element.~~

3. (Original) A solid state image pick-up device according to claim 2, wherein the active element comprises at least one selected from the group consisting of a transfer MOS transistor, a reset MOS transistor, a source follower input MOS transistor, and a selection MOS transistor.

4. (Currently Amended) A solid state image pick-up device according to claim 1, ~~further comprising: wherein in the~~ a pixel region, on the chip, in which pixels having an active element are two-dimensionally arranged, ~~[[;]]~~ and

~~an amplifier for amplifying signal charges successively read out from the pixels of the pixel region by the first scanning means and the second scanning means;~~

~~wherein the predetermined pad includes at least a pad through which a voltage is inputted to the amplifier or an output signal of the amplifier is outputted to the outside of the chip.~~

5. (Currently Amended) A solid state image pick-up device according to claim 2, wherein the pixel region is formed into a rectangle, and the ~~first scanning means~~ shift register is arranged closer to a long side of the pixel region.

6. (Currently Amended) A solid state image pick-up device according to claim 5, wherein the ~~plurality of first scanning means~~ are arranged to sandwich ~~therebetween~~ the pixel region is sandwiched by shift registers.

7. (Currently Amended) A solid state image pick-up device according to claim 2, wherein the first ~~scanning means~~ shift register ~~comprises~~ is a horizontal shift register, and the second ~~scanning means~~ shift register ~~is~~ comprises a vertical shift register.

8. (Original) A camera, comprising:

the solid state image pick-up device according to claim 1;

a lens for forming an optical image of a subject; and

a signal processing unit for processing a signal from the solid state image pick-up device.

9. (New) A solid state image pick-up device formed on a chip, comprising:

a pixel region;

a first shift register for reading a signal charge from the pixel region;

a second shift register having lower driving frequency than that of the first shift register, wherein the first and second shift registers are arranged along respectively different side portions of the chip;

an amplifier for amplifying the signal charge read from the pixel region by the first shift register; and

a pad for supplying a voltage to the amplifier, the pad being arranged along a side portion of the chip different from the side portion along which the first shift register is arranged.

10. (New) A solid state image pick-up device formed on a chip, comprising:

a pixel region;

a first shift register for reading a signal charge from the pixel region;

    a second shift register having a lower driving frequency than that of the first shift register, wherein the first and second shift registers are arranged along respectively different side portions of the chip;

    an amplifier for amplifying the signal charge read from the pixel region by the first shift register; and

    a pad for supplying a predetermined voltage or a ground voltage to an active element included in a pixel in the pixel region, the pad being arranged along a side portion of the chip different from the side portion along which the first shift register is arranged.

11. (New) The solid state image pick-up device according to claim 1, wherein the side portions along which the first and second shift registers are arranged are adjacent to each other.

12. (New) The solid state image pick-up device according to claim 9, wherein the side portions along which the first and second shift registers are arranged are adjacent to each other.

13. (New) The solid state image pick-up device according to claim 10, wherein the side portions along which the first and second shift registers are arranged are adjacent to each other.